TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC3074

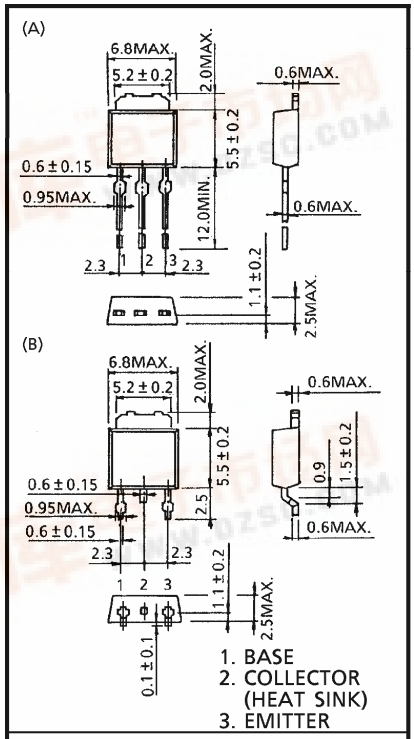
HIGH CURRENT SWITCHING APPLICATIONS

- Low Collector Saturation Voltage
  : $V_{CE\ (sat)}$ = 0.4 V (Max.) (at I_C = 3 A)
- High Speed Switching Time : t_{stg} = 1.0 μs (Typ.)
- Complementary to 2SA1244

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	60	V
Collector-Emitter Voltage		V_{CEO}	50	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current		I_C	5	A
Base Current		I_B	1	A
Collector Power Dissipation	Ta = 25°C	P_C	1.0	W
	Tc = 25°C		20	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

Unit in mm

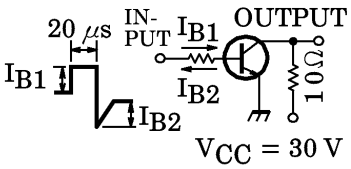


JEDEC	—
EIAJ	—
TOSHIBA	(A) 2-7B1A (B) 2-7B2A

Weight : 0.36 g

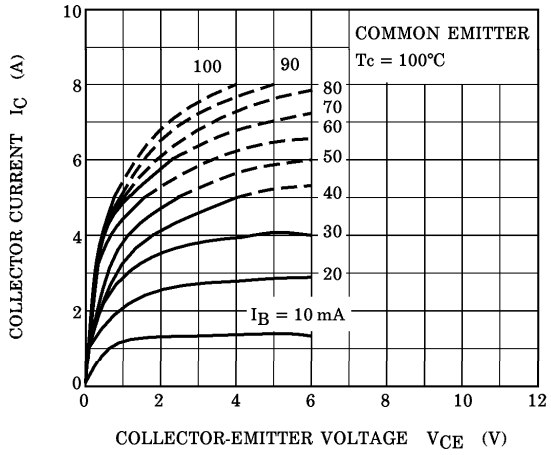
961001EAA1

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

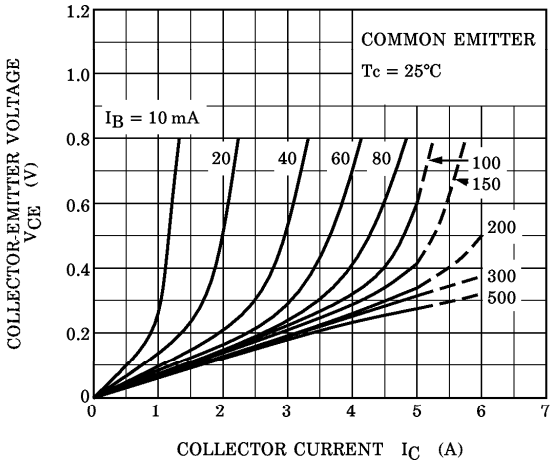
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB} = 50 V, I_E = 0	—	—	1	μA
Emitter Cut-off Current		I_{EBO}	V_{EB} = 5 V, I_C = 0	—	—	1	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C = 10 mA, I_B = 0	50	—	—	V
DC Current Gain		$h_{FE(1)}$ (Note)	V_{CE} = 1V, I_C = 1 A	70	—	240	
		$h_{FE(2)}$	V_{CE} = 1 V, I_C = 3 A	30	—	—	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	I_C = 3 A, I_B = 0.15 A	—	0.2	0.4	V
	Base-Emitter	$V_{BE(sat)}$	I_C = 3 A, I_B = 0.15 A	—	0.9	1.2	
Transition Frequency		f_T	V_{CE} = 4 V, I_C = 1 A	—	120	—	MHz
Collector Output Capacitance		C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz	—	80	—	pF
Switching Time	Turn-on Time	t_{on}		—	0.1	—	μs
	Storage Time	t_{stg}		—	1.0	—	
	Fall Time	t_f	$I_{B1} = -I_{B2}$ = 0.15 A, DUTY CYCLE ≦ 1%	—	0.1	—	

Note : $h_{FE(1)}$ Classification O : 70~140, Y : 120~240

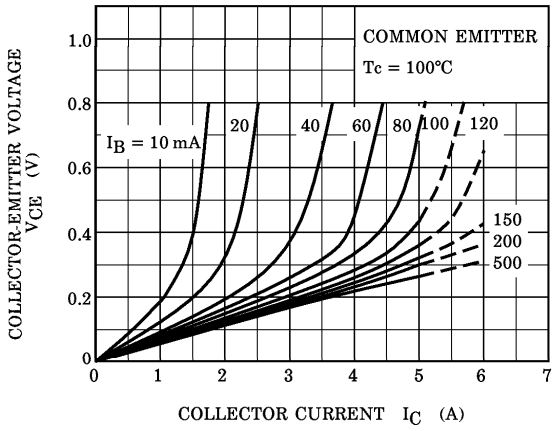
I_C – V_{CE}



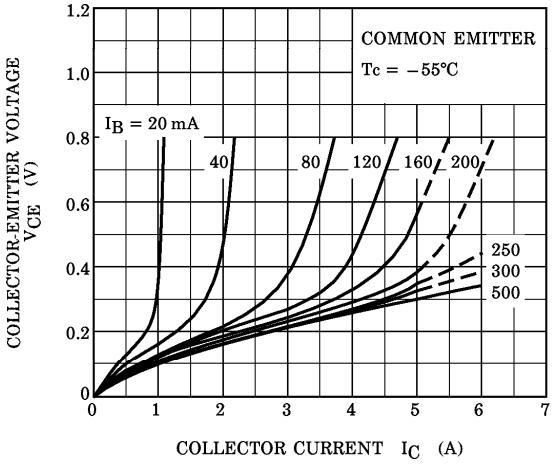
V_{CE} – I_C



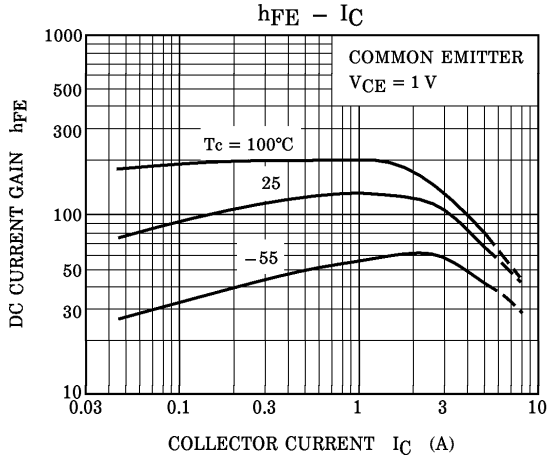
V_{CE} – I_C



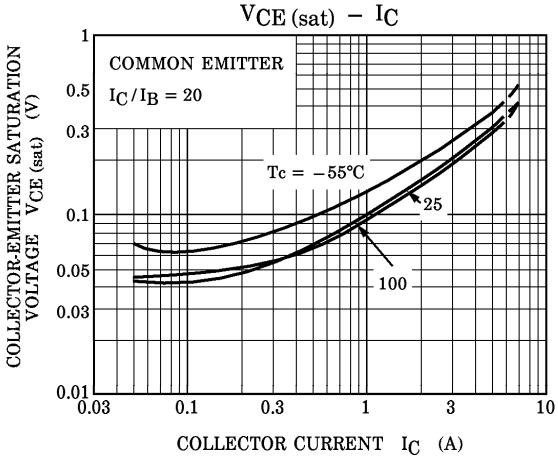
V_{CE} – I_C



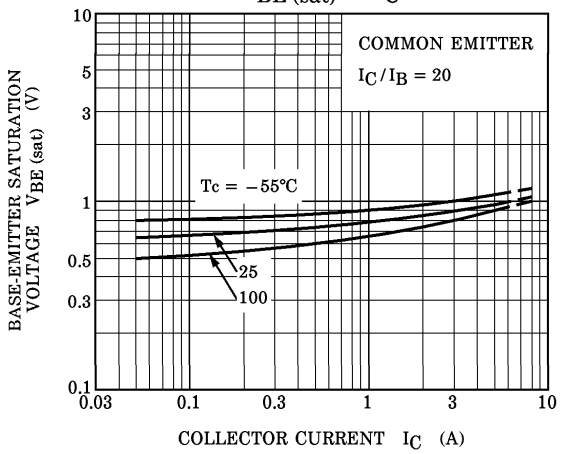
h_{FE} – I_C



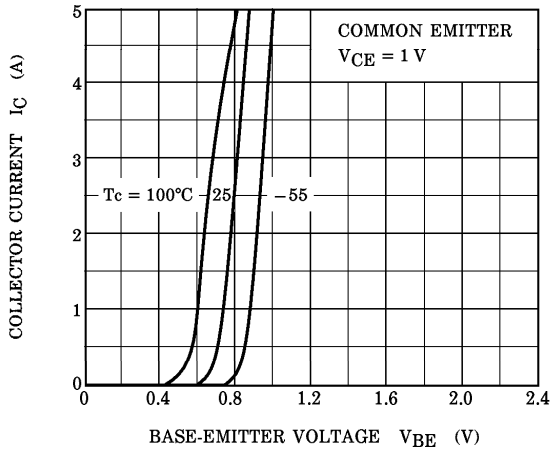
$V_{CE\,(sat)}$ – I_C



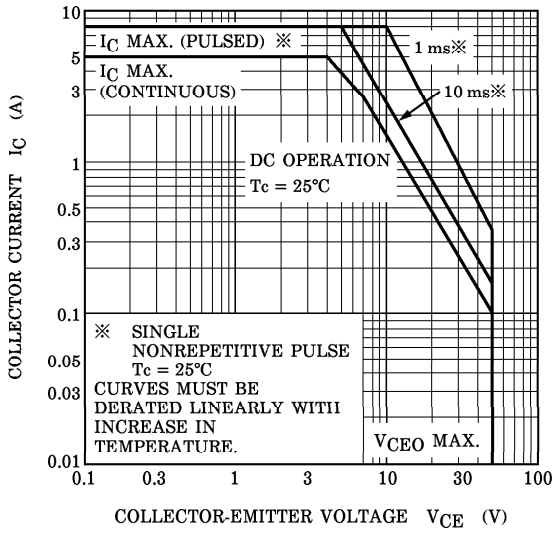
$V_{BE\,(sat)}$ – I_C



I_C – V_{BE}



SAFE OPERATING AREA



P_C – Ta